I hereby certify that this correspondence is being deposited with the United States Postal Service as first class mail in an envelope addressed to: Commissioner of Patents and Trademarks, Washington, D.C. 20231, on <u>September 26, 2003.</u> The applicant and/or attorney requests the date of deposit as the filing date. Depositor: Karen Cinq-Mars

SEP 2 9 2003

(Signature & da

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of

September 26, 2003

Huilong Zhu, et al.

Group Art Unit:

Serial No. Divisional Application of

10/605,130

Examiner:

Filed: 9/10/2003

International Business Machines Corporation

2070 Route 52

Hopewell Junction, NY 12533

TITLE:

STRUCTURE AND METHOD FOR SILICIDED METAL GATE TRANSISTORS

INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

Sir:

Pursuant to the duty of disclosure set forth in 37 C.F.R. 1.56, and further pursuant to the provisions of 37 C.F.R. 1.97 and 1.98, applicants hereby respectfully submit copies of the non-US patents and publications as listed on Form PTO-1449, attached hereto.

In citing these documents, no representation is made nor intended as to the pertinency or nonpertinency of the art, that better art than that listed is not available, or that other art is not applicable.

No fee is believed to be due for this submission. If any fees are required, however, the Commissioner is hereby authorized to charge such fees to Deposit Account No. 09-0458.

Respectfully submitted, Huilong Zhu, et al.

H. Daniel Schnumann, Agent

Registration No. 35,791

Telephone No. 845-894-2481

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EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.